



**NPN SILICON TRANSISTOR**  
**Qualified per MIL-PRF-19500/366**

*Qualified Levels:*  
 JAN, JANTX, JANTXV  
 and JANS

**DESCRIPTION**

This family of 2N3498L thru 2N3501L epitaxial planar transistors are military qualified up to a JANS level for high-reliability applications. These devices are also available in TO-39 and low profile U4 packaging. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

**FEATURES**

- JEDEC registered 2N3498 through 2N3501 series.
- JAN, JANTX, JANTXV, and JANS qualifications are available per MIL-PRF-19500/366. (See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

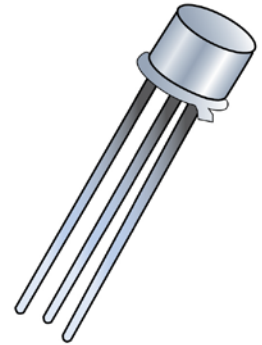
**APPLICATIONS / BENEFITS**

- General purpose transistors for medium power applications requiring high frequency switching.
- Low package profile.
- Military and other high-reliability applications.

**MAXIMUM RATINGS**

Parameters / Test Conditions	Symbol	2N3498L 2N3499L	2N3500L 2N3501L	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	150	V
Collector-Base Voltage	$V_{CBO}$	100	150	V
Emitter-Base Voltage	$V_{EBO}$	6.0	6.0	V
Collector Current	$I_C$	500	300	mA
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	175		$^{\circ}C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	30		$^{\circ}C/W$
Total Power Dissipation @ $T_A = +25^{\circ}C$ <sup>(1)</sup> @ $T_C = +25^{\circ}C$ <sup>(2)</sup>	$P_T$	1.0 5.0		W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^{\circ}C$

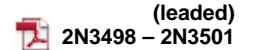
- Notes:** 1. See [figure 1](#).  
 2. See [figure 2](#).



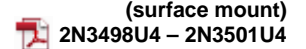
**TO-5 Package**

Also available in:

**TO-39 (TO-205AD) package**



**U4 package**



**MSC – Lawrence**

6 Lake Street,  
 Lawrence, MA 01841  
 Tel: 1-800-446-1158 or  
 (978) 620-2600  
 Fax: (978) 689-0803

**MSC – Ireland**

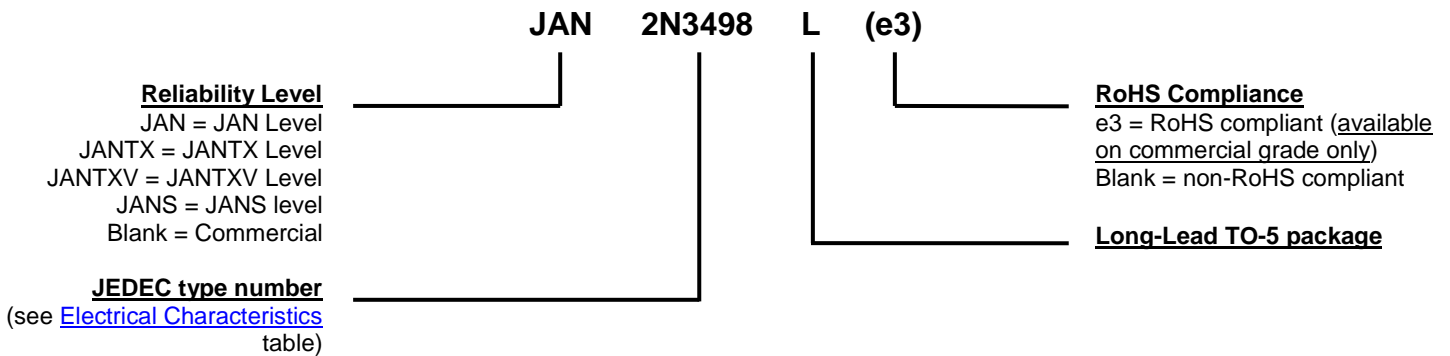
Gort Road Business Park,  
 Ennis, Co. Clare, Ireland  
 Tel: +353 (0) 65 6840044  
 Fax: +353 (0) 65 6822298

**Website:**

[www.microsemi.com](http://www.microsemi.com)

**MECHANICAL and PACKAGING**

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Leads are kovar, nickel plated, and finish is solder dip (Sn63/Pb37). Can be RoHS compliant with pure matte-tin (commercial grade only).
- MARKING: Part number, date code, manufacturer's ID.
- WEIGHT: Approximately 1.14 grams.
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$C_{obo}$	Common-base open-circuit output capacitance
$I_{CEO}$	Collector cutoff current, base open
$I_{CEX}$	Collector cutoff current, circuit between base and emitter
$I_{EBO}$	Emitter cutoff current, collector open
$h_{FE}$	Common-emitter static forward current transfer ratio
$V_{CEO}$	Collector-emitter voltage, base open
$V_{CBO}$	Collector-emitter voltage, emitter open
$V_{EBO}$	Emitter-base voltage, collector open

**ELECTRICAL CHARACTERISTICS @  $T_A = +25\text{ }^\circ\text{C}$ , unless otherwise noted**

Characteristic	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage $I_C = 10\text{ mA}$ , pulsed	$V_{(BR)CEO}$	100		V
2N3498L, 2N3499L 2N3500L, 2N3501L		150		
Collector-Base Cutoff Current $V_{CB} = 50\text{ V}$	$I_{CBO}$		50	nA
$V_{CB} = 75\text{ V}$			50	nA
$V_{CB} = 100\text{ V}$			10	$\mu\text{A}$
$V_{CB} = 150\text{ V}$			10	$\mu\text{A}$
Emitter-Base Cutoff Current $V_{EB} = 4.0\text{ V}$	$I_{EBO}$		25	nA
$V_{EB} = 6.0\text{ V}$			10	$\mu\text{A}$

**ON CHARACTERISTICS <sup>(1)</sup>**

Forward-Current Transfer Ratio $I_C = 0.1\text{ mA}$ , $V_{CE} = 10\text{ V}$	2N3498L, 2N3500L 2N3499L, 2N3501L 2N3498L, 2N3500L 2N3499L, 2N3501L 2N3498L, 2N3500L 2N3499L, 2N3501L 2N3498L, 2N3500L 2N3499L, 2N3501L 2N3500L 2N3501L 2N3498L 2N3499L	$h_{FE}$	20		
$I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ V}$			35		
$I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$			25		
$I_C = 150\text{ mA}$ , $V_{CE} = 10\text{ V}$			50		
$I_C = 300\text{ mA}$ , $V_{CE} = 10\text{ V}$			35		
$I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ V}$			75		
			40	120	
	100	300			
	15				
	20				
	15				
	20				
Collector-Emitter Saturation Voltage $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$	All Types 2N3498L, 2N3499L 2N3500L, 2N3501L	$V_{CE(sat)}$		0.2	V
$I_C = 300\text{ mA}$ , $I_B = 30\text{ mA}$				0.6	
$I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$				0.4	
Base-Emitter Saturation Voltage $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$	All Types 2N3498L, 2N3499L 2N3500L, 2N3501L	$V_{BE(sat)}$		0.8	V
$I_C = 300\text{ mA}$ , $I_B = 30\text{ mA}$				1.4	
$I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$				1.2	

**DYNAMIC CHARACTERISTICS**

Forward Current Transfer Ratio, Magnitude $I_C = 20\text{ mA}$ , $V_{CE} = 20\text{ V}$ , $f = 100\text{ MHz}$	$ h_{fe} $	1.5	8.0	
Output Capacitance $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	$C_{obo}$		10	pF
			8.0	
Input Capacitance $V_{EB} = 0.5\text{ V}$ , $I_C = 0$ , $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	$C_{ibo}$		80	pF

(1) Pulse Test: pulse width = 300  $\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

**ELECTRICAL CHARACTERISTICS** ( $T_A = +25\text{ }^\circ\text{C}$ , unless otherwise noted)

**SWITCHING CHARACTERISTICS**

Characteristic	Symbol	Min.	Max.	Unit
Turn-On Time $V_{EB} = 5\text{ V}; I_C = 150\text{ mA}; I_{B1} = 15\text{ mA}$	$t_{on}$		115	ns
Turn-Off Time $I_C = 150\text{ mA}; I_{B1} = I_{B2} = -15\text{ mA}$	$t_{off}$		1150	ns

**SAFE OPERATING AREA** (See SOA figure and reference [MIL-STD-750 method 3053](#))

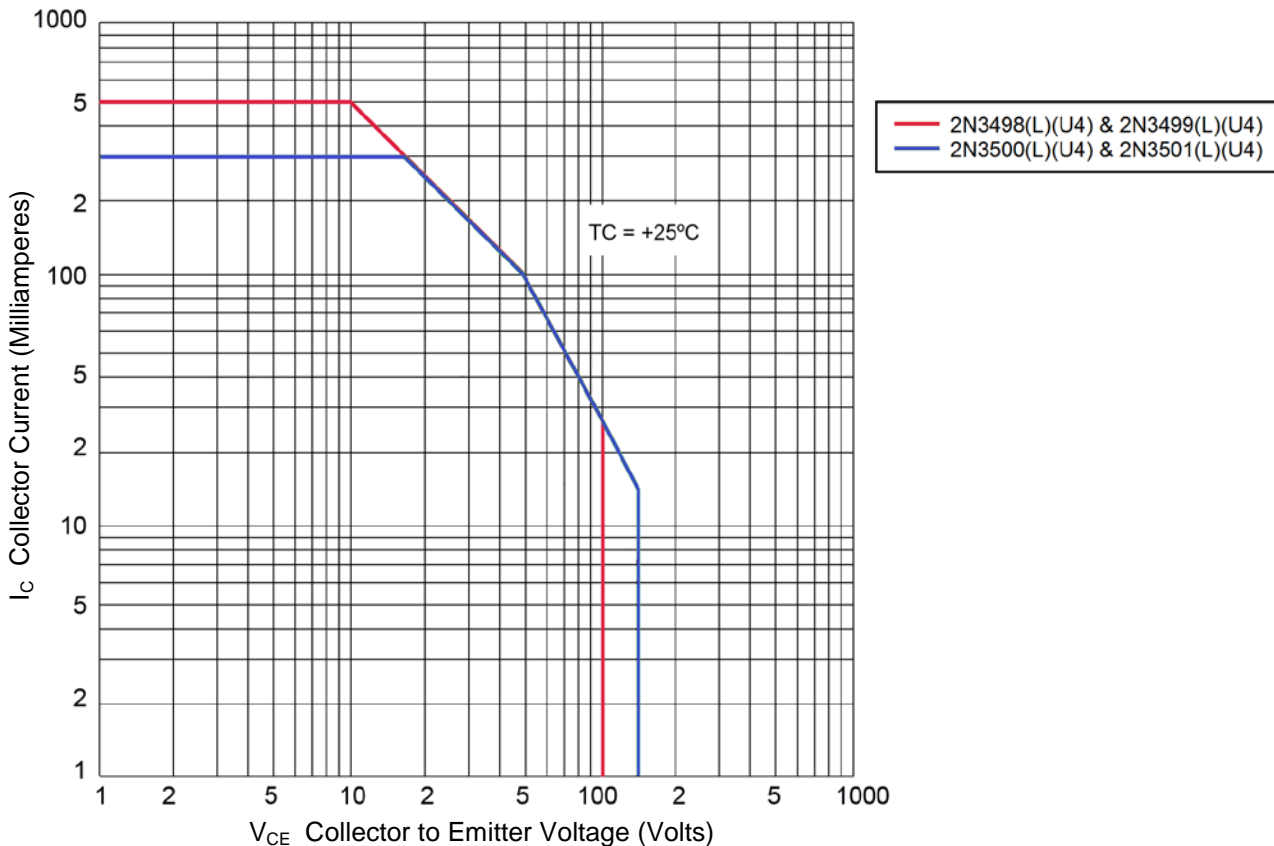
**DC Tests**
 $T_C = +25\text{ }^\circ\text{C}$ ,  $t_r \geq 10\text{ ns}$ ; 1 Cycle,  $t = 1.0\text{ s}$ 
**Test 1**
 $V_{CE} = 10\text{ V}, I_C = 500\text{ mA}$       2N3498L, 2N3499L

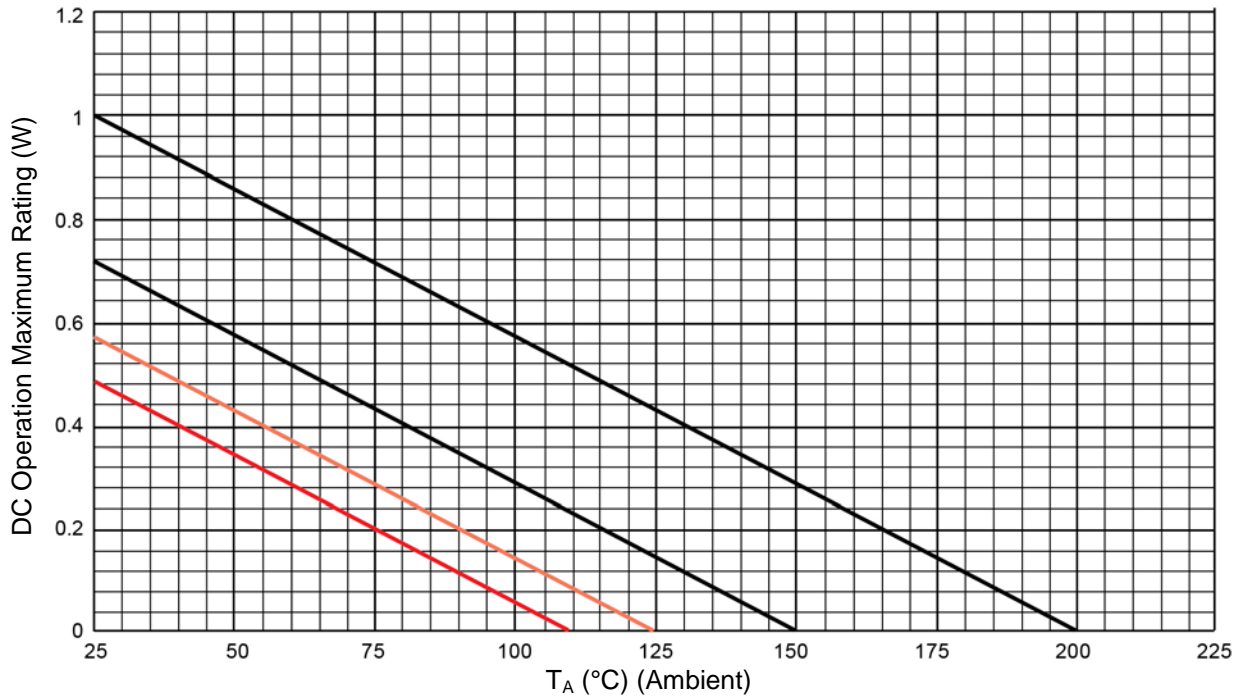
 $V_{CE} = 16.67\text{ V}, I_C = 300\text{ mA}$       2N3500L, 2N3501L

**Test 2**
 $V_{CE} = 50\text{ V}, I_C = 100\text{ mA}$       All Types

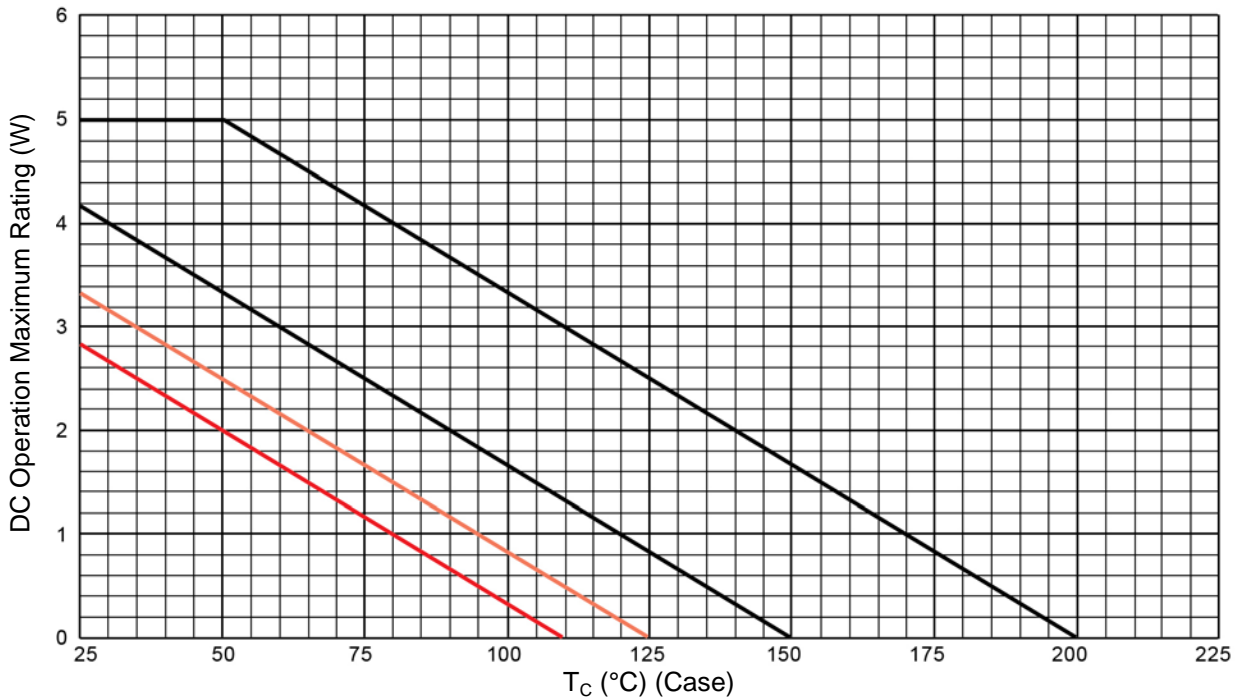
**Test 3**
 $V_{CE} = 80\text{ V}, I_C = 40\text{ mA}$       All Types

**Clamped Switching**
 $T_A = +25\text{ }^\circ\text{C}$ 
**Test 1**
 $I_B = 85\text{ mA}, I_C = 500\text{ mA}$       2N3498L, 2N3499L

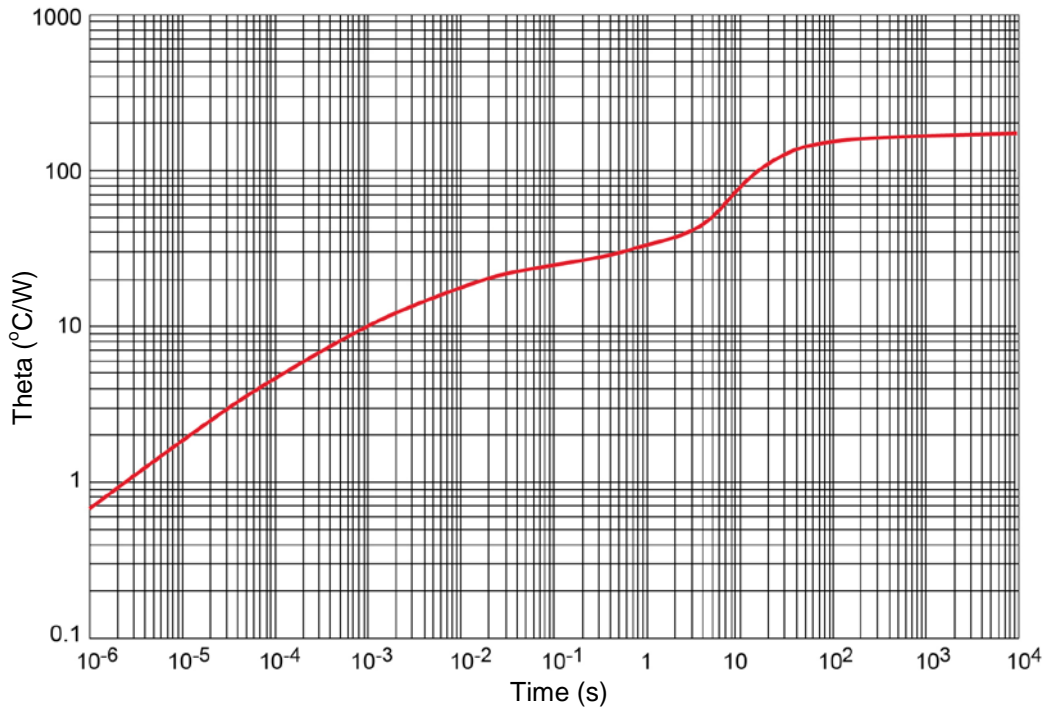
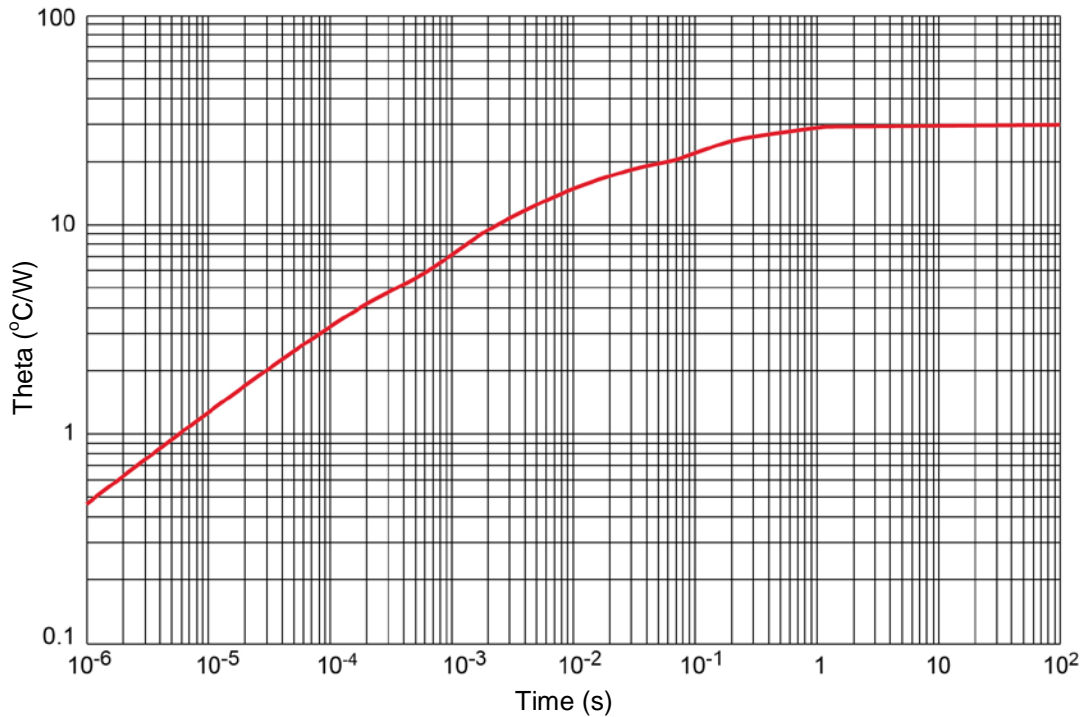
 $I_B = 50\text{ mA}, I_C = 300\text{ mA}$       2N3500L, 2N3501L


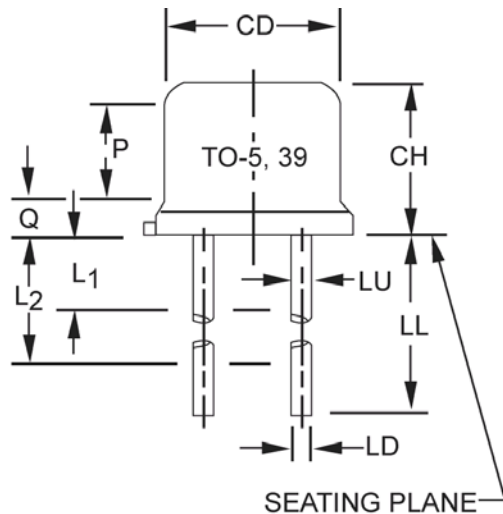
**GRAPHS**

**FIGURE 1**

Derating for all devices ( $R_{\theta JA}$ )


**FIGURE 2**

Derating for all devices ( $R_{\theta JC}$ )

**GRAPHS**

**FIGURE 3**
Thermal impedance graph ( $R_{\theta JA}$ )

**FIGURE 4**
Thermal impedance graph ( $R_{\theta JC}$ )

**PACKAGE DIMENSIONS**


Symbol	Dimensions				Note
	Inch		Millimeters		
	Min	Max	Min	Max	
<b>CD</b>	0.305	0.335	7.75	8.51	
<b>CH</b>	0.240	0.260	6.10	6.60	
<b>HD</b>	0.335	0.370	8.51	9.40	
<b>LC</b>	0.200 TP		5.08 TP		6
<b>LD</b>	0.016	0.021	0.41	0.53	7
<b>LL</b>	See notes 7, 12 and 13				
<b>LU</b>	0.016	0.019	0.41	0.48	7, 13
<b>L1</b>		0.050		1.27	13
<b>L2</b>	0.250		6.35		13
<b>P</b>	0.100		2.54		5
<b>Q</b>		0.050		1.27	4
<b>TL</b>	0.029	0.045	0.74	1.14	3
<b>TW</b>	0.028	0.034	0.71	0.86	10, 11
<b>r</b>		0.010		0.25	11
<b>α</b>	45° TP		45° TP		6

**NOTES:**

- Dimensions are in inches.
- Millimeters are given for general information only.
- Symbol TL is measured from HD maximum.
- Details of outline in this zone are optional.
- Symbol CD shall not vary more than .010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 inch (1.37 mm) +.001 inch (0.03 mm) -.000 inch (0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) relative to tab. Device may be measured by direct methods or by gauge.
- Symbol LD applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Lead diameter shall not exceed .042 inch (1.07 mm) within L1 and beyond LL minimum.
- Lead designation, shall be as follows: 1 - emitter, 2 - base, 3 - collector.
- Lead number three is electrically connected to case.
- Beyond r maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- Symbol r applied to both inside corners of tab.
- For transistor types 2N3498, 2N3499, 2N3500, and 2N3501, LL = .50 inch (12.7 mm) minimum and .750 inch (19.1 mm) maximum. For transistor types 2N3498L, 2N3499L, 2N3500L, and 2N3501L, LL = 1.50 inches (38.1 mm) minimum and 1.750 inches (44.5 mm) maximum.
- All three leads.
- In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi$ x symbology.

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## Microchip:

[JANS2N3499L/TR](#) [JANS2N3499L](#) [Jantx2N3499L/TR](#) [JANTXV2N3498L/TR](#) [2N3499L/TR](#) [JAN2N3500L/TR](#)  
[Jantxv2N3499L/TR](#) [JANTX2N3498L/TR](#) [Jan2N3501L/TR](#) [Jan2N3499L/TR](#) [JANTX2N3500L/TR](#) [2N3501L/TR](#)  
[JANTXV2N3500L/TR](#) [JAN2N3498L/TR](#) [2N3498L/TR](#)



## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9